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1N6101

$B_V > 75V$, at $5\mu A$
 $I_r < 100nA$ at $40V$
 $C < 4.0 pF$

Diode Array

Absolute Maximum Ratings:

Symbol	Parameter	Limit	Unit
$V_{BR}(R)$ *1 *2	Reverse Breakdown Voltage	75	Vdc
I_O *1 *3	Continuous Forward Current	300	mAdc
I_{FSM} *1	Peak Surge Current ($t_p = 1/120$ s)	500	mAdc
PT1 *4	Power Dissipation per Junction @ 25°C	400	mW
PT2 *4	Power Dissipation per Package @ 25°C	600	mW
Top	Operating Junction Temperature Range	-65 to +150	°C
Tstg	Storage Temperature Range	-65 to +200	°C

NOTE 1: Each Diode

NOTE 2: Pulsed: PW = 100ms max.; duty cycle $\leq 20\%$

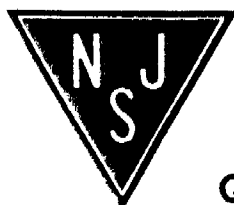
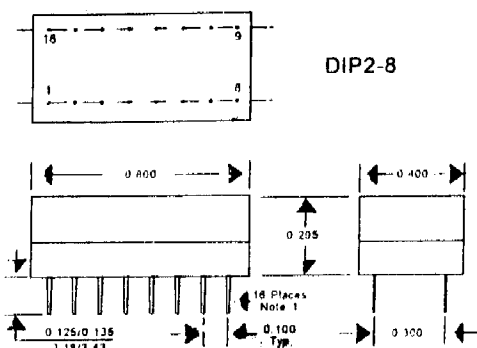
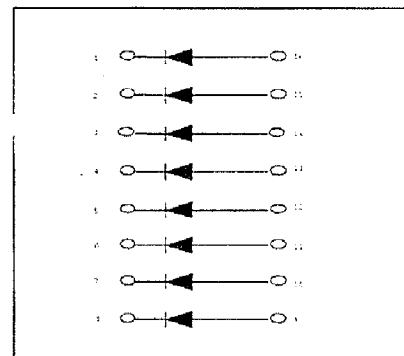
NOTE 3: Derate at $2.4mA/^\circ C$ above +25 °C

NOTE 4: Derate at $4.0mW/^\circ C$ above +25 °C

Electrical Characteristics (Per Diode) @ 25°C unless otherwise specified

Symbol	Parameter	Conditions	Min	Max	Unit
V_{F1}	Forward Voltage	$I_f = 100mAdc$ *1		1	Vdc
I_{R1}	Reverse Current	$V_R = 40 Vdc$		0.1	μAdc
i_{R2}	Reverse Current	$V_R = 20 Vdc$		25	nAdc
C_t	Capacitance (pin to pin)	$V_R = 0Vdc$; $f = 1 MHz$		4.0	pF
t_{fr}	Forward Recovery Time	$I_f = 100mAdc$		15	ns
t_{rr}	Reverse Recovery Time	$I_f = I_R = 10mAdc$, $i_{rr} = 1 mAdc$, $R_L = 100 ohms$		10	ns
V_{F5}	Forward Voltage Match	$I_f = 10 mA$		5	mV

NOTE 1: Pulsed: PW = 300us +/- 50us, duty cycle $\leq 2\%$, 90us after leading edge



Quality Semi-Conductors